650V Super Junction MOSFET

DESCRIPTION：

·Low RDS(on) per chip area(Low FOM)

·Very low switching and conduction loss

·Excellent ESD robustness

·Extremely high commutation ruggedness

·100% avalanche tested

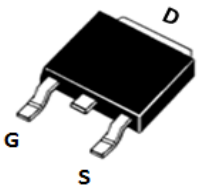
V_{DSS}	650V
I_D @V_{GS}=10V	10.6A
$R_{DS(ON)_Typ.}$ @V_{GS}=10V	334mΩ

TYPICAL APPLICATIONS：

·TV and PC Power

·Adopter and Lighting

·Telecom and UPS(Uninterruptible Power Supply)



TO-252

MAXIMUM RATINGS (at T_C = 25 °C, unless otherwise specified)

Characteristic	Condition	Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	650	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	Tc=25℃ Tc=100℃	I_D	10.6 6.7	A
Pulsed Drain Current		I_{DM}	31.8	A
Avalanche Energy, Single Pulse (3)	Starting Tj = 25˚C, IAS = 4.5A,VDD = 50V, ID = IAR	E_{AS}	171	mJ
Power Dissipation		Ptot	83.3	W
Reverse Diode dv/dt		dv/dt	15	V/ns
Junction & Storage temperature Range		T_J, T_{STG}	-55~+150	℃
Thermal resistance,	Junction to Ambient Junction to Case	$R_{\theta JA}$ $R_{\theta JC}$	62.5 1.5	℃/W

ELECTRICAL CHARATERISTICS (at T_J = 25 °C, unless otherwise specified)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage VGS = 0V, ID = 250uA	$V_{(BR)DSS}$	650			V
Gate-Source threshold voltage VDS = VGS, ID = 250uA	$V_{GS(th)}$	2.5	3.5	4.5	V
Gate-Source Leakage Current VGS = ±20V, VDS = 0V	I_{GSS}			1	uA
Zero Gate Voltage Drain Current VDS = 650 V, VGS = 0 V ,Tj=25℃	I_{DSS}			1	uA
Drain-Source On-State Resistance VGS = 10V, ID = 5.3A,	$R_{DS(on)}$		334	380	mΩ
Input capacitance f=250KHz, VDS=400 V, VGS=0 V	C_{iss}		733		pF
Output capacitance f=250KHz, VDS=400 V, VGS=0 V	C_{oss}		18.6		pF
Reverse transfer capacitance f=250KHz, VDS=400 V, VGS=0 V	C_{rss}		1.6		pF
Effective Output Capacitance, Energy Related VGS=10V, VDS=0 to 400V	$C_{O(er)}$		28.6		pF
Effective Output Capacitance, Time Related VGS=10V, VDS=0 to 400V	$C_{O(tr)}$		141		pF
Turn-on delay time VDD=325 V, ID=5.3A, VGS=10V, R_{GEN}=20Ω	$td_{(ON)}$		18.4		ns
Rise time VDD=325 V, ID=5.3A, VGS=10V, R_{GEN}=20Ω	tr		95.2		ns
Turn-off delay time VDD=325 V, ID=5.3A, VGS=10V, R_{GEN}=20Ω	$td_{(OFF)}$		61.6		ns
Fall time VDD=325 V, ID=5.3A, VGS=10V, R_{GEN}=20Ω	tf		23.2		ns
Gate Resistance f=1MHz	R_g		16		Ω
Total Gate Charge VDS= 520V, ID= 5.3A,VGS= 10V	Q_G		19		nC
Gate to Source Charge VDS= 520V, ID= 5.3A,VGS= 10V	Q_{GS}		4		nC
Gate to Drain Charge VDS= 520V, ID= 5.3A,VGS= 10V	Q_{GD}		9		nC
Diode Forward Voltage VGS = 0V, I_S =5.3A	V_{SD}			1.4	V
Continuous Diode forward current	I_{SD}			10.6	A
Revers Recovery Time V_{DS}=100V,I_{SD}=5.3A, di_F/dt = 100A/us	Trr		208		ns
Peak Reverse Recovery Current V_{DS}=100V,I_{SD}=5.3A, di_F/dt = 100A/us	Irrm		15.5		A
Revers Recovery Charge V_{DS}=100V,I_{SD}=5.3A, di_F/dt = 100A/us	Qrr		1.61		nC

Typical Performance Characteristics

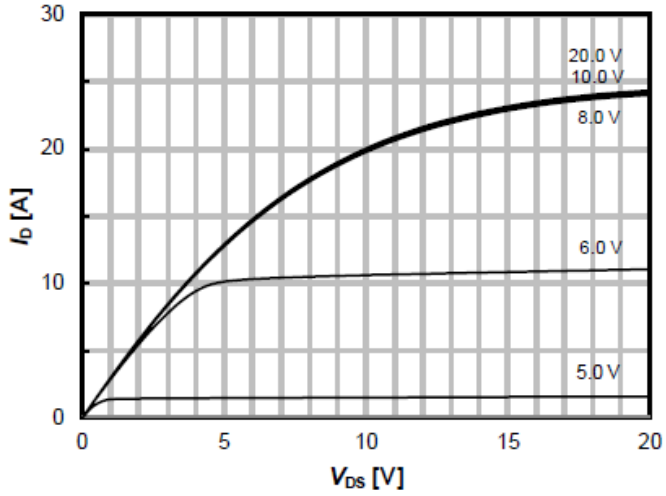


Figure 1. Output Characteristics

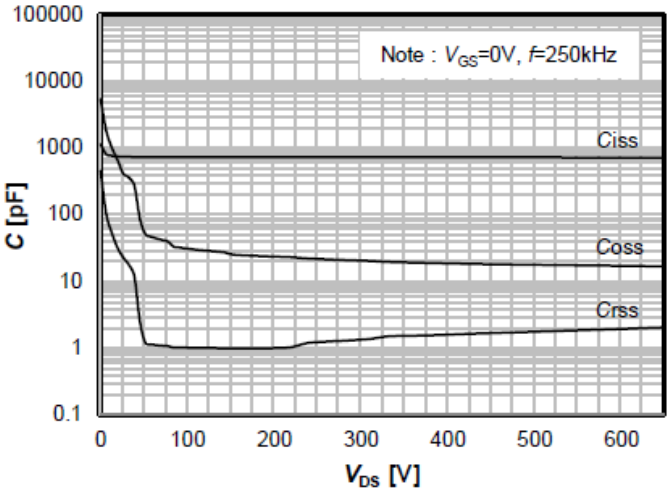


Figure 2. Capacitances

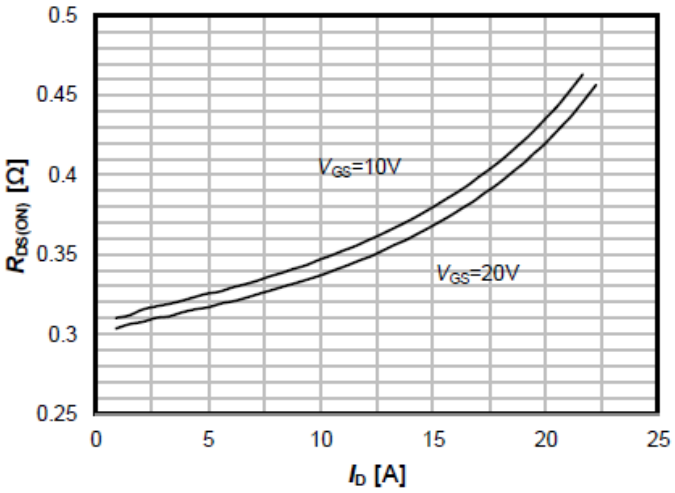


Figure 3. On-state Resistance

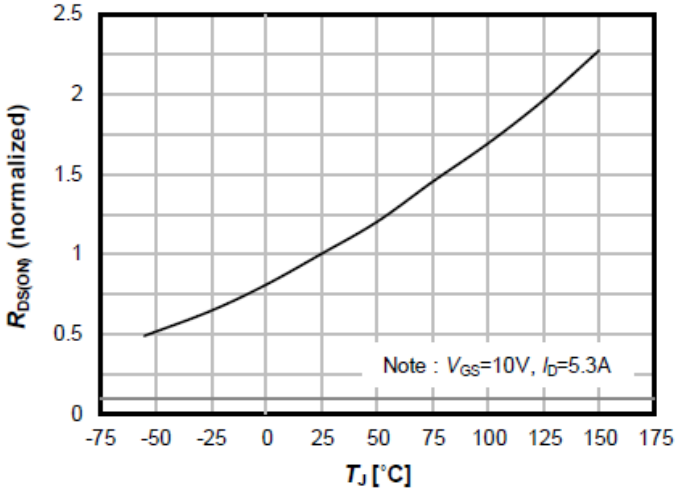


Figure 4. On-state Resistance with Temperature

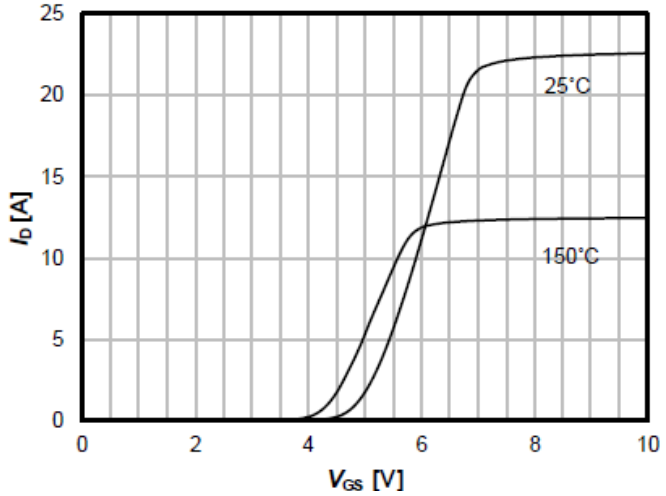


Figure 5. Transfer Characteristics

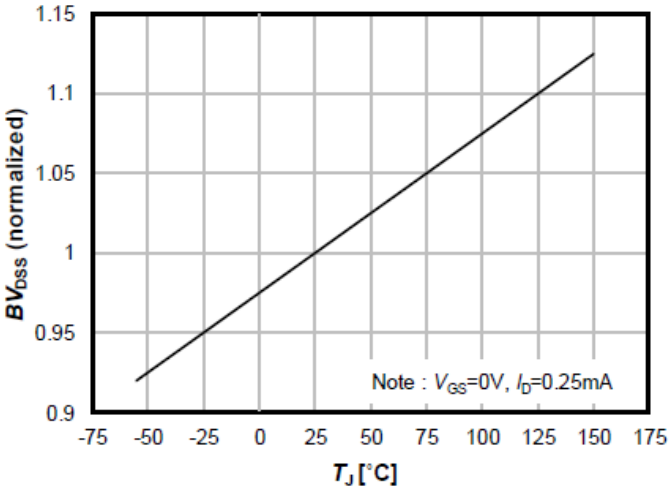


Figure 6. Breakdown Voltage with Temperature

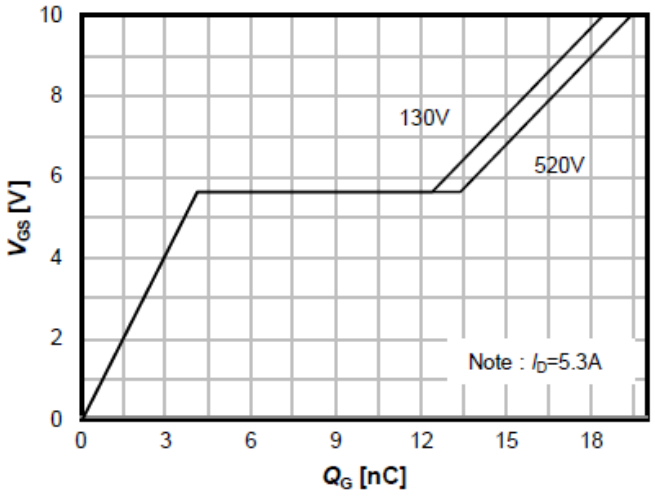


Figure 7. Gate Charge

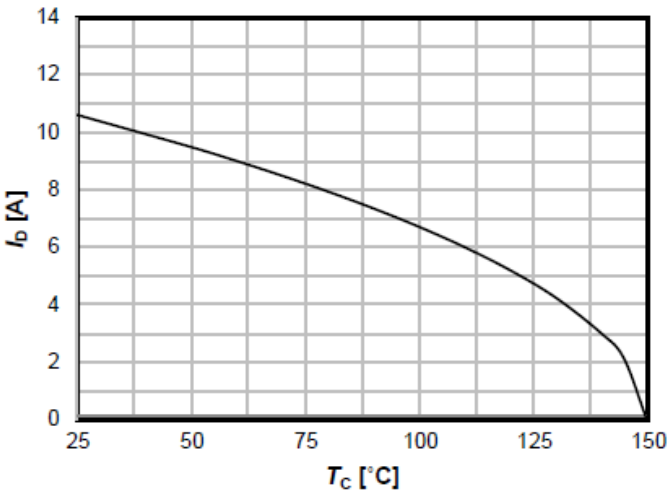


Figure8. Maximum Drain Current

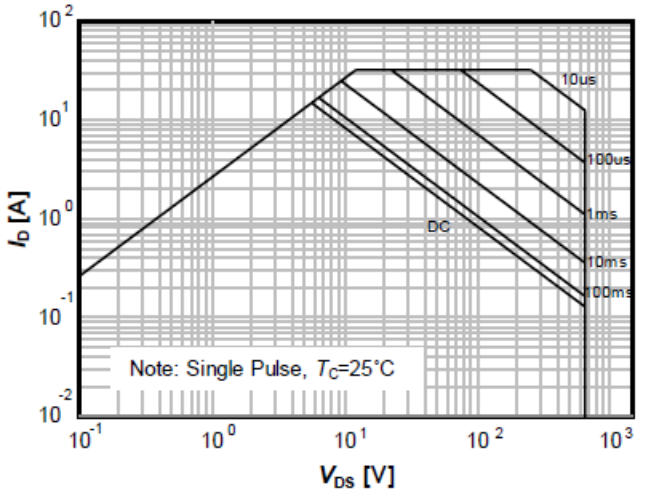


Figure 9. Safe Operating Area

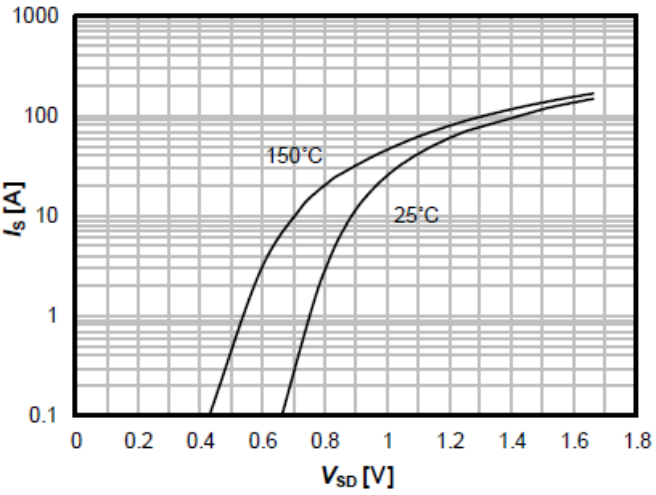


Figure 10. Body Diode Characteristics

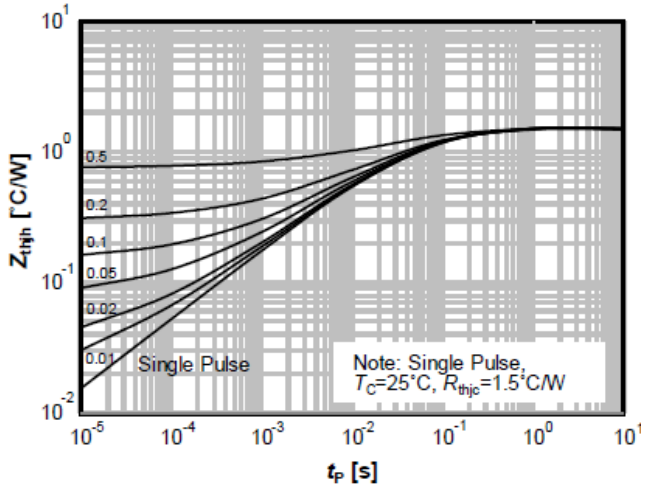


Figure 11. Maximum Transient Thermal Characteristics

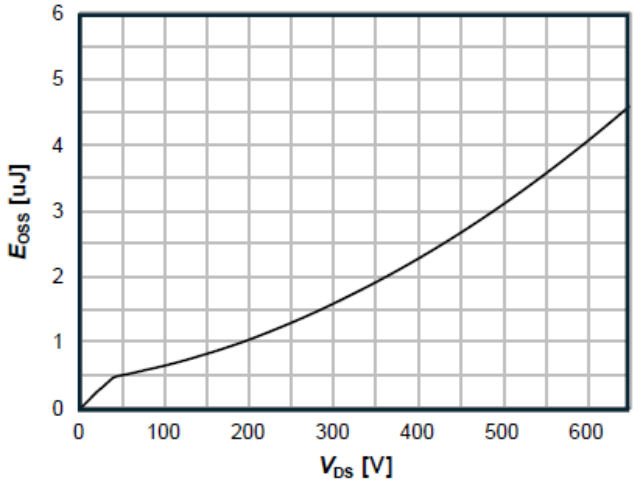
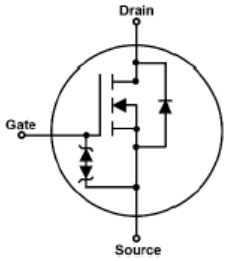


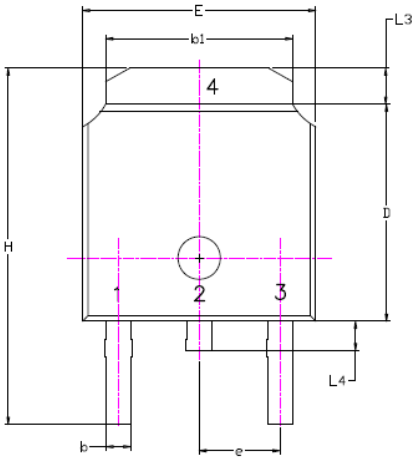
Figure 12. Coss Stored Energy

·Circuit diagram

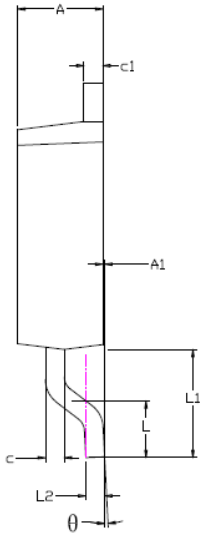


·Package outlines : Dimensions in (mm)

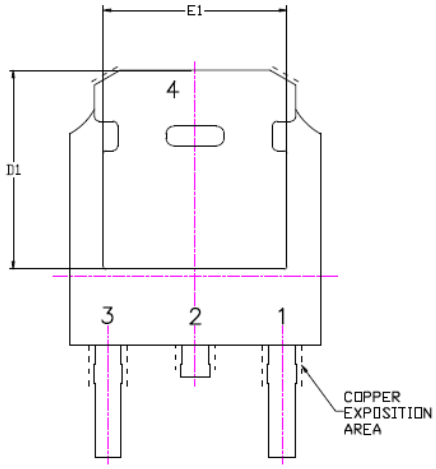
Top view



Side view



Bottom view



SYMBOL	DIMENSIONAL REQMTS	
	MIN.	MAX.
A	2.20	2.40
A1	0.00	0.127
b	0.635	0.889
b1	5.17	5.42
c	0.46	0.60
c1	0.46	0.58
D	6.00	6.20
D1	5.15 REF	
E	6.50	6.70
E1	4.83 REF	
e	2.286 BSC	
H	9.40	10.40
L	1.40	1.70
L1	2.90 REF	
L2	0.508 BSC	
L3	0.89	1.27
L4	0.64	1.01
θ	0°	10°

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